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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Obsolete
Core Processor	C166SV2
Core Size	16-Bit
Speed	80MHz
Connectivity	EBI/EMI, I <sup>2</sup> C, LINbus, SPI, SSC, UART/USART, USI
Peripherals	I <sup>2</sup> S, POR, PWM, WDT
Number of I/O	40
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	18K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 9x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP Exposed Pad
Supplier Device Package	PG-LQFP-64-6
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/sak-xe162hn-16f80l-aa



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### **Summary of Features**

- On-Chip Peripheral Modules
  - Two synchronizable A/D Converters with up to 9 channels, 10-bit resolution, conversion time below 1 μs, optional data preprocessing (data reduction, range check), broken wire detection
  - 16-channel general purpose capture/compare unit (CC2)
  - One capture/compare units for flexible PWM signal generation (CCU60)
  - Multi-functional general purpose timer unit with 5 timers
  - 6 serial interface channels to be used as UART, LIN, high-speed synchronous channel (SPI/QSPI), IIC bus interface (10-bit addressing, 400 kbit/s), IIS interface
  - On-chip MultiCAN interface (Rev. 2.0B active) with 64 message objects (Full CAN/Basic CAN) on up to 2 CAN nodes and gateway functionality
  - On-chip system timer and on-chip real time clock
- Single power supply from 3.0 V to 5.5 V
- Power reduction and wake-up modes
- · Programmable watchdog timer and oscillator watchdog
- Up to 40 general purpose I/O lines
- · On-chip bootstrap loaders
- Supported by a full range of development tools including C compilers, macroassembler packages, emulators, evaluation boards, HLL debuggers, simulators, logic analyzer disassemblers, programming boards
- · On-chip debug support via Device Access Port (DAP) or JTAG interface
- 64-pin Green LQFP package, 0.5 mm (19.7 mil) pitch

## **Ordering Information**

The ordering code for an Infineon microcontroller provides an exact reference to a specific product. This ordering code identifies:

- the derivative itself, i.e. its function set, the temperature range, and the supply voltage
- · the temperature range:
  - SAF-...: -40°C to 85°C
  - SAK-...: -40°C to 125°C
- · the package and the type of delivery.

For ordering codes for the XE162xN please contact your sales representative or local distributor.



#### **General Device Information**

Table 5 Pin Definitions and Functions (cont'd)

Pin	Symbol	Ctrl.	Туре	Function					
28	P2.3	O0 / I	St/B	Bit 3 of Port 2, General Purpose Input/Output					
	U0C0_DOUT	01	St/B	USIC0 Channel 0 Shift Data Output					
	CC2_CC16	O3 / I	St/B	CAPCOM2 CC16IO Capture Inp./ Compare Out.					
	ESR2_0	I	St/B	ESR2 Trigger Input 0					
	U0C0_DX0E	I	St/B	USIC0 Channel 0 Shift Data Input					
	U0C1_DX0D	I	St/B	USIC0 Channel 1 Shift Data Input					
	RxDC0A	I	St/B	CAN Node 0 Receive Data Input					
29	P2.4	O0 / I	St/B	Bit 4 of Port 2, General Purpose Input/Output					
	U0C1_DOUT	01	St/B	USIC0 Channel 1 Shift Data Output					
	TxDC0	O2	St/B	CAN Node 0 Transmit Data Output					
	CC2_CC17	O3 / I	St/B	CAPCOM2 CC17IO Capture Inp./ Compare Out.					
	ESR1_0	I	St/B	ESR1 Trigger Input 0					
	U0C0_DX0F	I	St/B	USIC0 Channel 0 Shift Data Input					
	RxDC1A	I	St/B	CAN Node 1 Receive Data Input					
30	P2.5	O0 / I	St/B	Bit 5 of Port 2, General Purpose Input/Output					
	U0C0_SCLK OUT	01	St/B	USIC0 Channel 0 Shift Clock Output					
	TxDC0	O2	St/B	CAN Node 0 Transmit Data Output					
	CC2_CC18	O3 / I	St/B	CAPCOM2 CC18IO Capture Inp./ Compare Out.					
	U0C0_DX1D	I	St/B	USIC0 Channel 0 Shift Clock Input					
	ESR1_10	I	St/B	ESR1 Trigger Input 10					
31	P2.6	O0 / I	St/B	Bit 6 of Port 2, General Purpose Input/Output					
	U0C0_SELO 0	01	St/B	USIC0 Channel 0 Select/Control 0 Output					
	U0C1_SELO 1	O2	St/B	USIC0 Channel 1 Select/Control 1 Output					
	CC2_CC19	O3 / I	St/B	CAPCOM2 CC19IO Capture Inp./ Compare Out.					
	U0C0_DX2D	I	St/B	USIC0 Channel 0 Shift Control Input					
	RxDC0D	I	St/B	CAN Node 0 Receive Data Input					
	ESR2_6	I	St/B	ESR2 Trigger Input 6					



#### **General Device Information**

Table 5 Pin Definitions and Functions (cont'd)

Pin	Symbol	Ctrl.	Туре	Function
35	P2.7	00 / 1		Bit 7 of Port 2, General Purpose Input/Output
33				
	U0C1_SELO 0	01	St/B	USIC0 Channel 1 Select/Control 0 Output
	U0C0_SELO 1	O2	St/B	USIC0 Channel 0 Select/Control 1 Output
	CC2_CC20	O3 / I	St/B	CAPCOM2 CC20IO Capture Inp./ Compare Out.
	U0C1_DX2C	I	St/B	USIC0 Channel 1 Shift Control Input
	RxDC1C	I	St/B	CAN Node 1 Receive Data Input
	ESR2_7	I	St/B	ESR2 Trigger Input 7
36	P2.8	O0 / I	DP/B	Bit 8 of Port 2, General Purpose Input/Output
	U0C1_SCLK OUT	01	DP/B	USIC0 Channel 1 Shift Clock Output
	EXTCLK	O2	DP/B	Programmable Clock Signal Output
	CC2_CC21	O3 / I	DP/B	CAPCOM2 CC21IO Capture Inp./ Compare Out.
	U0C1_DX1D	I	DP/B	USIC0 Channel 1 Shift Clock Input
37	P2.9	O0 / I	St/B	Bit 9 of Port 2, General Purpose Input/Output
	U0C1_DOUT	01	St/B	USIC0 Channel 1 Shift Data Output
	TxDC1	O2	St/B	CAN Node 1 Transmit Data Output
	CC2_CC22	O3 / I	St/B	CAPCOM2 CC22IO Capture Inp./ Compare Out.
	CLKIN1	I	St/B	Clock Signal Input 1
	TCK_A	IH	St/B	DAP0/JTAG Clock Input  If JTAG pos. A is selected during start-up, an internal pull-up device will hold this pin high when nothing is driving it.  If DAP pos. 0 is selected during start-up, an internal pull-down device will hold this pin low when nothing is driving it.



#### **General Device Information**

Table 5 Pin Definitions and Functions (cont'd)

Pin	Symbol	Ctrl.	Туре	Function
38	P10.0	O0 / I	St/B	Bit 0 of Port 10, General Purpose Input/Output
	U0C1_DOUT	01	St/B	USIC0 Channel 1 Shift Data Output
	CCU60_CC6	O2	St/B	CCU60 Channel 0 Output
	CCU60_CC6 0INA	I	St/B	CCU60 Channel 0 Input
	ESR1_2	I	St/B	ESR1 Trigger Input 2
	U0C0_DX0A	I	St/B	USIC0 Channel 0 Shift Data Input
	U0C1_DX0A	1	St/B	USIC0 Channel 1 Shift Data Input
39	P10.1	O0 / I	St/B	Bit 1 of Port 10, General Purpose Input/Output
	U0C0_DOUT	01	St/B	USIC0 Channel 0 Shift Data Output
	CCU60_CC6	O2	St/B	CCU60 Channel 1 Output
	CCU60_CC6 1INA	I	St/B	CCU60 Channel 1 Input
	U0C0_DX1A	I	St/B	USIC0 Channel 0 Shift Clock Input
	U0C0_DX0B	I	St/B	USIC0 Channel 0 Shift Data Input
40	P10.2	O0 / I	St/B	Bit 2 of Port 10, General Purpose Input/Output
	U0C0_SCLK OUT	O1	St/B	USIC0 Channel 0 Shift Clock Output
	CCU60_CC6	O2	St/B	CCU60 Channel 2 Output
	CCU60_CC6 2INA	I	St/B	CCU60 Channel 2 Input
	U0C0_DX1B	I	St/B	USIC0 Channel 0 Shift Clock Input
42	P2.10	O0 / I	St/B	Bit 10 of Port 2, General Purpose Input/Output
	U0C1_DOUT	01	St/B	USIC0 Channel 1 Shift Data Output
	U0C0_SELO 3	O2	St/B	USIC0 Channel 0 Select/Control 3 Output
	CC2_CC23	O3 / I	St/B	CAPCOM2 CC23IO Capture Inp./ Compare Out.
	U0C1_DX0E	I	St/B	USIC0 Channel 1 Shift Data Input
	CAPINA	I	St/B	GPT12E Register CAPREL Capture Input



## **General Device Information**

Table 5 Pin Definitions and Functions (cont'd)

Pin	Symbol	Ctrl.	Туре	pe Function				
2, 16, 18,	$V_{DDPB}$	-	PS/B	Digital Pad Supply Voltage for Domain B Connect decoupling capacitors to adjacent $V_{\rm DDP}/V_{\rm SS}$ pin pairs as close as possible to the pins.				
32, 34, 48, 50, 64				Note: The on-chip voltage regulators and all ports except P5, P6 and P15 are fed from supply voltage $V_{\rm DDPB}$ .				
1, 17, 33,	$V_{\rm SS}$	-	PS/	<b>Digital Ground</b> All $V_{\rm SS}$ pins must be connected to the ground-line or ground-plane.				
49				Note: Also the exposed pad is connected internally to $V_{\rm SS}$ . To improve the EMC behavior, it is recommended to connect the exposed pad to the board ground. For thermal aspects, please refer to the Data Sheet. Board layout examples are given in an application note.				

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**Functional Description** 

## 3 Functional Description

The architecture of the XE162xN combines advantages of RISC, CISC, and DSP processors with an advanced peripheral subsystem in a well-balanced design. On-chip memory blocks allow the design of compact systems-on-silicon with maximum performance suited for computing, control, and communication.

The on-chip memory blocks (program code memory and SRAM, dual-port RAM, data SRAM) and the generic peripherals are connected to the CPU by separate high-speed buses. Another bus, the LXBus, connects additional on-chip resources and external resources. This bus structure enhances overall system performance by enabling the concurrent operation of several subsystems of the XE162xN.

The block diagram gives an overview of the on-chip components and the advanced internal bus structure of the XE162xN.

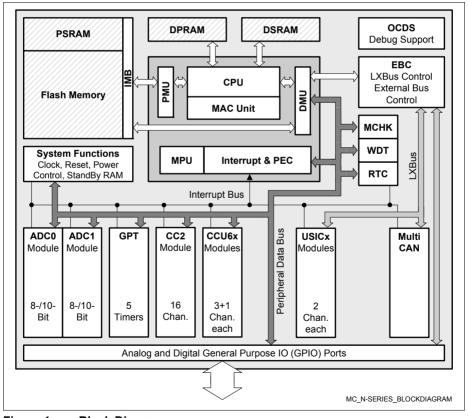


Figure 4 Block Diagram



#### **Functional Description**

### **Memory Content Protection**

The contents of on-chip memories can be protected against soft errors (induced e.g. by radiation) by activating the parity mechanism or the Error Correction Code (ECC).

The parity mechanism can detect a single-bit error and prevent the software from using incorrect data or executing incorrect instructions.

The ECC mechanism can detect and automatically correct single-bit errors. This supports the stable operation of the system.

It is strongly recommended to activate the ECC mechanism wherever possible because this dramatically increases the robustness of an application against such soft errors.



### **Functional Description**

## 3.2 Central Processing Unit (CPU)

The core of the CPU consists of a 5-stage execution pipeline with a 2-stage instruction-fetch pipeline, a 16-bit arithmetic and logic unit (ALU), a 32-bit/40-bit multiply and accumulate unit (MAC), a register-file providing three register banks, and dedicated SFRs. The ALU features a multiply-and-divide unit, a bit-mask generator, and a barrel shifter.

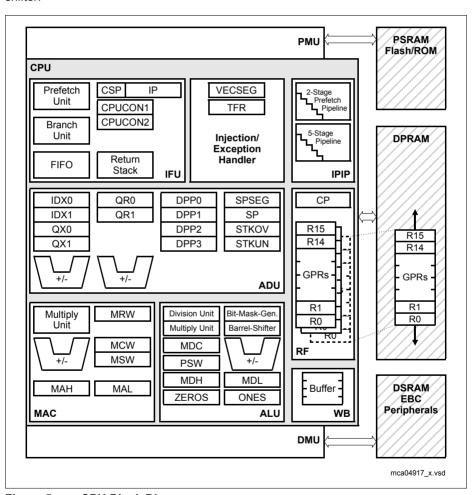


Figure 5 CPU Block Diagram



### **Functional Description**

to a dedicated vector table location). The occurrence of a hardware trap is also indicated by a single bit in the trap flag register (TFR). Unless another higher-priority trap service is in progress, a hardware trap will interrupt any ongoing program execution. In turn, hardware trap services can normally not be interrupted by standard or PEC interrupts.

Depending on the package option up to 3 External Service Request (ESR) pins are provided. The ESR unit processes their input values and allows to implement user controlled trap functions (System Requests SR0 and SR1). In this way reset, wakeup and power control can be efficiently realized.

Software interrupts are supported by the 'TRAP' instruction in combination with an individual trap (interrupt) number. Alternatively to emulate an interrupt by software a program can trigger interrupt requests by writing the Interrupt Request (IR) bit of an interrupt control register.

## 3.6 On-Chip Debug Support (OCDS)

The On-Chip Debug Support system built into the XE162xN provides a broad range of debug and emulation features. User software running on the XE162xN can be debugged within the target system environment.

The OCDS is controlled by an external debugging device via the debug interface. This either consists of the 2-pin Device Access Port (DAP) or of the JTAG port conforming to IEEE-1149. The debug interface can be completed with an optional break interface.

The debugger controls the OCDS with a set of dedicated registers accessible via the debug interface (DAP or JTAG). In addition the OCDS system can be controlled by the CPU, e.g. by a monitor program. An injection interface allows the execution of OCDS-generated instructions by the CPU.

Multiple breakpoints can be triggered by on-chip hardware, by software, or by an external trigger input. Single stepping is supported, as is the injection of arbitrary instructions and read/write access to the complete internal address space. A breakpoint trigger can be answered with a CPU halt, a monitor call, a data transfer, or/and the activation of an external signal.

Tracing of data can be obtained via the debug interface, or via the external bus interface for increased performance.

Tracing of program execution is supported by the XE166 Family emulation device. With this device the DAP can operate on clock rates of up to 20 MHz.

The DAP interface uses two interface signals, the JTAG interface uses four interface signals, to communicate with external circuitry. The debug interface can be amended with two optional break lines.

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### **Functional Description**

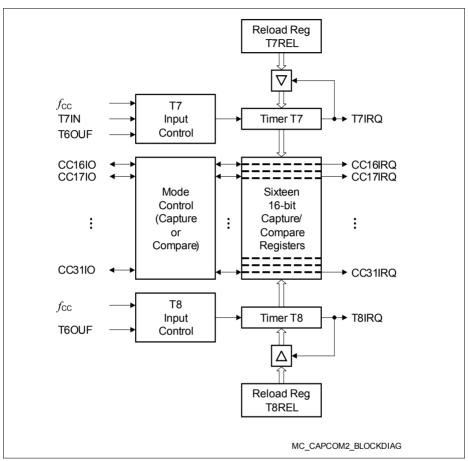


Figure 6 CAPCOM Unit Block Diagram

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### **Functional Description**

## 3.8 Capture/Compare Units CCU6x

The XE162xN types feature the CCU60 unit(s).

CCU6 is a high-resolution capture and compare unit with application-specific modes. It provides inputs to start the timers synchronously, an important feature in devices with several CCU6 modules.

The module provides two independent timers (T12, T13), that can be used for PWM generation, especially for AC motor control. Additionally, special control modes for block commutation and multi-phase machines are supported.

#### **Timer 12 Features**

- Three capture/compare channels, where each channel can be used either as a capture or as a compare channel.
- Supports generation of a three-phase PWM (six outputs, individual signals for highside and low-side switches)
- 16-bit resolution, maximum count frequency = peripheral clock
- · Dead-time control for each channel to avoid short circuits in the power stage
- Concurrent update of the required T12/13 registers
- Center-aligned and edge-aligned PWM can be generated
- · Single-shot mode supported
- Many interrupt request sources
- · Hysteresis-like control mode
- Automatic start on a HW event (T12HR, for synchronization purposes)

#### **Timer 13 Features**

- One independent compare channel with one output
- 16-bit resolution, maximum count frequency = peripheral clock
- Can be synchronized to T12
- Interrupt generation at period match and compare match
- Single-shot mode supported
- Automatic start on a HW event (T13HR, for synchronization purposes)

#### **Additional Features**

- Block commutation for brushless DC drives implemented
- Position detection via Hall sensor pattern
- Automatic rotational speed measurement for block commutation
- Integrated error handling
- Fast emergency stop without CPU load via external signal (CTRAP)
- · Control modes for multi-channel AC drives
- Output levels can be selected and adapted to the power stage



#### **Electrical Parameters**

#### 4.3 DC Parameters

These parameters are static or average values that may be exceeded during switching transitions (e.g. output current).

The XE162xN can operate within a wide supply voltage range from 3.0 V to 5.5 V. However, during operation this supply voltage must remain within 10 percent of the selected nominal supply voltage. It cannot vary across the full operating voltage range.

Because of the supply voltage restriction and because electrical behavior depends on the supply voltage, the parameters are specified separately for the upper and the lower voltage range.

During operation, the supply voltages may only change with a maximum speed of dV/dt < 1 V/ms.

Leakage current is strongly dependent on the operating temperature and the voltage level at the respective pin. The maximum values in the following tables apply under worst case conditions, i.e. maximum temperature and an input level equal to the supply voltage.

The value for the leakage current in an application can be determined by using the respective leakage derating formula (see tables) with values from that application.

The pads of the XE162xN are designed to operate in various driver modes. The DC parameter specifications refer to the pad current limits specified in **Section 4.7.4**.



#### **Electrical Parameters**

Table 16 DC Characteristics for Lower Voltage Range (cont'd)

Parameter	Symbol		Value	s	Unit	Note / Test Condition
		Min.	Тур.	Max.		
Output High voltage <sup>7)</sup>	$V_{OH}CC$	V <sub>DDP</sub> - 1.0	_	-	V	$I_{\mathrm{OH}} \geq I_{\mathrm{OHmax}}$
		V <sub>DDP</sub> - 0.4	-	-	V	$I_{\text{OH}} \ge I_{\text{OHnom}}^{8)}$
Output Low Voltage <sup>7)</sup>	$V_{OL}CC$	-	_	0.4	V	$I_{\rm OL} \le I_{\rm OLnom}^{8)}$
		_	-	1.0	٧	$I_{OL} \leq I_{OLmax}$

- 1) Because each double bond pin is connected to two pads (standard pad and high-speed pad), it has twice the normal value. For a list of affected pins refer to the pin definitions table in chapter 2.
- Not subject to production test verified by design/characterization. Hysteresis is implemented to avoid metastable states and switching due to internal ground bounce. It cannot suppress switching due to external system noise under all conditions.
- 3) If the input voltage exceeds the respective supply voltage due to ground bouncing  $(V_{\rm IN} < V_{\rm SS})$  or supply ripple  $(V_{\rm IN} > V_{\rm DDP})$ , a certain amount of current may flow through the protection diodes. This current adds to the leakage current. An additional error current  $(I_{\rm INJ})$  will flow if an overload current flows through an adjacent pin. Please refer to the definition of the overload coupling factor  $K_{\rm CIV}$ .
- 4) The given values are worst-case values. In production test, this leakage current is only tested at 125 °C; other values are ensured by correlation. For derating, please refer to the following descriptions: Leakage derating depending on temperature (T<sub>J</sub> = junction temperature [°C]): I<sub>OZ</sub> = 0.05 x e<sup>(1.5 + 0.028 x TJ-)</sup> [μA]. For example, at a temperature of 95 °C the resulting leakage current is 3.2 μA. Leakage derating depending on voltage level (DV = V<sub>DDP</sub> V<sub>PIN</sub> [V]): I<sub>OZ</sub> = I<sub>OZtempmax</sub> (1.6 x DV) (μA]. This voltage derating formula is an approximation which applies for maximum temperature.
- 5) Drive the indicated minimum current through this pin to change the default pin level driven by the enabled pull device: V<sub>PIN</sub> <= V<sub>IL</sub> for a pullup; V<sub>PIN</sub> >= V<sub>IH</sub> for a pulldown.
- 6) Limit the current through this pin to the indicated value so that the enabled pull device can keep the default pin level: V<sub>PIN</sub> >= V<sub>IH</sub> for a pullup; V<sub>PIN</sub> <= V<sub>II</sub> for a pulldown.
- 7) The maximum deliverable output current of a port driver depends on the selected output driver mode. This specification is not valid for outputs which are switched to open drain mode. In this case the respective output will float and the voltage is determined by the external circuit.
- 8) As a rule, with decreasing output current the output levels approach the respective supply level ( $V_{\rm OL}$ -> $V_{\rm SS}$ ,  $V_{\rm OH}$ -> $V_{\rm DDP}$ ). However, only the levels for nominal output currents are verified.



#### **Electrical Parameters**

Table 17 Switching Power Consumption

Parameter	Symbol		Values		Unit	Note /
		Min.	Тур.	Max.		Test Condition
Power supply current (active) with all peripherals active and EVVRs on	I <sub>SACT</sub> CC	_	6 + 0.6 $x f_{SYS}^{1)}$	8 + 1.0 $x f_{SYS}^{1)}$	mA	power_mode= active; voltage_range= both <sup>2)3)4)</sup>
Power supply current in stopover mode, EVVRs on	I <sub>SSO</sub> CC	_	0.7	2.0	mA	power_mode= stopover; voltage_range= both 4)

<sup>1)</sup>  $f_{SYS}$  in MHz

- 3) Please consider the additional conditions described in section "Active Mode Power Supply Current".
- 4) The pad supply voltage has only a minor influence on this parameter.

### **Active Mode Power Supply Current**

The actual power supply current in active mode not only depends on the system frequency but also on the configuration of the XE162xN's subsystem.

Besides the power consumed by the device logic the power supply pins also provide the current that flows through the pin output drivers.

A small current is consumed because the drivers' input stages are switched.

The IO power domains can be supplied separately. Power domain A ( $V_{\rm DDPA}$ ) supplies the A/D converters and Port 6. Power domain B ( $V_{\rm DDPB}$ ) supplies the on-chip EVVRs and all other ports.

During operation domain A draws a maximum current of 1.5 mA for each active A/D converter module from  $V_{\rm DDPA}$ .

In Fast Startup Mode (with the Flash modules deactivated), the typical current is reduced to  $3 + 0.6 \times f_{SYS}$  mA.

<sup>2)</sup> The pad supply voltage pins (V<sub>DDPB</sub>) provide the input current for the on-chip EVVRs and the current consumed by the pin output drivers. A small current is consumed because the drivers input stages are switched. In Fast Startup Mode (with the Flash modules deactivated), the typical current is reduced to 3 + 0.6 x f<sub>SVS</sub>.

#### **Electrical Parameters**

## 4.6 Flash Memory Parameters

The XE162xN is delivered with all Flash sectors erased and with no protection installed. The data retention time of the XE162xN's Flash memory (i.e. the time after which stored data can still be retrieved) depends on the number of times the Flash memory has been erased and programmed.

Note: These parameters are not subject to production test but verified by design and/or characterization.

Note: Operating Conditions apply.

Table 24 Flash Parameters

Parameter	Symbol		Values	5	Unit	Note /
		Min.	Тур.	Max.		Test Condition
Parallel Flash module	$N_{\mathrm{PP}}\mathrm{SR}$	_	_	2 <sup>1)</sup>		$N_{\text{FL\_RD}} \le 1$
program/erase limit depending on Flash read activity		_	_	1 <sup>2)</sup>		<i>N</i> <sub>FL_RD</sub> > 1
Flash erase endurance for security pages	$N_{\mathrm{SEC}}\mathrm{SR}$	10	-	_	cycles	t <sub>RET</sub> ≥ 20 years
Flash wait states <sup>3)</sup>	$N_{\mathrm{WSFLAS}}$	1	_	_		f <sub>SYS</sub> ≤ 8 MHz
	<sub>H</sub> SR	2	_	_		f <sub>SYS</sub> ≤ 13 MHz
		3	_	_		$f_{\rm SYS} \le$ 17 MHz
		4	_	_		$f_{\rm SYS}$ > 17 MHz
Erase time per sector/page	$t_{ER}CC$	_	7 <sup>4)</sup>	8.0	ms	
Programming time per page	$t_{PR}CC$	_	3 <sup>4)</sup>	3.5	ms	
Data retention time	$t_{RET}CC$	20	-	_	years	$N_{\rm ER} \le$ 1,000 cycl es
Drain disturb limit	$N_{\mathrm{DD}}\mathrm{SR}$	32	_	_	cycles	
Number of erase cycles	$N_{ER}SR$	_	_	15.000	cycles	$t_{\rm RET} \ge 5$ years; Valid for Flash module 1 (up to 64 kbytes)
		_	_	1.000	cycles	t <sub>RET</sub> ≥ 20 years

The unused Flash module(s) can be erased/programmed while code is executed and/or data is read from only
one Flash module or from PSRAM. The Flash module that delivers code/data can, of course, not be
erased/programmed.



#### **Electrical Parameters**

Table 35 JTAG Interface Timing for Upper Voltage Range (cont'd)

Parameter	Symbol		Values		Unit	Note /
		Min.	Тур.	Max.		Test Condition
TCK low time	t <sub>3</sub> SR	16	_	_	ns	
TCK clock rise time	t <sub>4</sub> SR	_	_	8	ns	
TCK clock fall time	t <sub>5</sub> SR	_	_	8	ns	
TDI/TMS setup to TCK rising edge	t <sub>6</sub> SR	6	_	_	ns	
TDI/TMS hold after TCK rising edge	t <sub>7</sub> SR	6	_	_	ns	
TDO valid from TCK falling edge (propagation delay) <sup>2)</sup>	t <sub>8</sub> CC	_	25	29	ns	
TDO high impedance to valid output from TCK falling edge <sup>3)2)</sup>	t <sub>9</sub> CC	-	25	29	ns	
TDO valid output to high impedance from TCK falling edge <sup>2)</sup>	t <sub>10</sub> CC	_	25	29	ns	
TDO hold after TCK falling edge <sup>2)</sup>	t <sub>18</sub> CC	5	_	_	ns	

<sup>1)</sup> Under typical conditions, the JTAG interface can operate at transfer rates up to 20 MHz.

**Table 36** is valid under the following conditions:  $C_1 = 20 \text{ pF}$ ; voltage\_range= lower

Table 36 JTAG Interface Timing for Lower Voltage Range

Parameter	Symbol		Values	S	Unit	Note / Test Condition
		Min.	Тур.	Max.		
TCK clock period	t <sub>1</sub> SR	50	_	_	ns	
TCK high time	t <sub>2</sub> SR	16	_	_	ns	
TCK low time	t <sub>3</sub> SR	16	_	_	ns	
TCK clock rise time	t <sub>4</sub> SR	-	_	8	ns	
TCK clock fall time	t <sub>5</sub> SR	-	_	8	ns	
TDI/TMS setup to TCK rising edge	t <sub>6</sub> SR	6	_	_	ns	

<sup>2)</sup> The falling edge on TCK is used to generate the TDO timing.

<sup>3)</sup> The setup time for TDO is given implicitly by the TCK cycle time.



#### **Electrical Parameters**

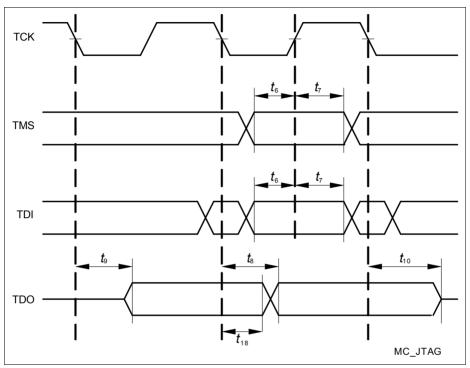


Figure 27 JTAG Timing

### Package and Reliability

## 5 Package and Reliability

The XE166 Family devices use the package type PG-LQFP (Plastic Green - Low Profile Quad Flat Package). The following specifications must be regarded to ensure proper integration of the XE162xN in its target environment.

### 5.1 Packaging

These parameters specify the packaging rather than the silicon.

Table 37 Package Parameters (PG-LQFP-64-6)

Parameter	Symbol	Limit Values		Unit	Notes
		Min.	Max.		
Exposed Pad Dimension	Ex × Ey	_	5.6 × 5.6	mm	_
Power Dissipation	$P_{DISS}$	_	0.8	W	_
Thermal resistance Junction-Ambient	$R_{\Theta \sf JA}$	-	40	K/W	No thermal via <sup>1)</sup>
			37	K/W	4-layer, no pad <sup>2)</sup>
			25	K/W	4-layer, pad <sup>3)</sup>

<sup>1)</sup> Device mounted on a 4-layer board without thermal vias; exposed pad not soldered.

Note: To improve the EMC behavior, it is recommended to connect the exposed pad to the board ground, independent of the thermal requirements.

Board layout examples are given in an application note.

## Package Compatibility Considerations

The XE162xN is a member of the XE166 Family of microcontrollers. It is also compatible to a certain extent with members of similar families or subfamilies.

Each package is optimized for the device it houses. Therefore, there may be slight differences between packages of the same pin-count but for different device types. In particular, the size of the Exposed Pad (if present) may vary.

If different device types are considered or planned for an application, it must be ensured that the board layout fits all packages under consideration.

Device mounted on a 4-layer JEDEC board (according to JESD 51-7) with thermal vias; exposed pad not soldered.

Device mounted on a 4-layer JEDEC board (according to JESD 51-7) with thermal vias; exposed pad soldered to the board.